

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of  
KOCHERGIN ET AL.

Serial No. 10/686,519

Filed: 16 October 2003



Atty. Ref.: 340-81

TC/A.U.: 2872

Examiner:

For: METHOD OF MANUFACTURING A SPECTRAL FILTER FOR  
GREEN AND LONGER WAVELENGTHS

\* \* \* \* \*

March 22, 2004

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

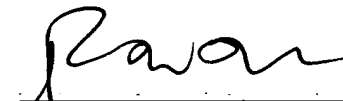
**INFORMATION DISCLOSURE STATEMENT**

In accordance with Rule 97, the undersigned attorney submits the documents listed on the attached form PTO-1449. A copy of each non-U.S. patent document is enclosed.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy to the undersigned as an indication that the attached documents have been considered and made of record in this case.

Respectfully submitted,

**NIXON & VANDERHYE P.C.**

By: 

Robert W. Faris  
Reg. No. 31,352

RWF:ejs  
1100 North Glebe Road, 8th Floor  
Arlington, VA 22201-4714  
Telephone: (703) 816-4000  
Facsimile: (703) 816-4100

**INFORMATION DISCLOSURE  
CITATION**

ATTY. DOCKET NO.

SERIAL NO.

340-81

10/686,519

APPLICANT

KOCHERGIN ET AL.

(Use several sheets if necessary)

FILING DATE

TC/A.U.

16 October 2003

2872


**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	4,874,484	10/1989	Foell et al.			
	5,262,021	11/1993	V. Lehmann et al.			
	5,348,627	09/1994	Propst et al.			
	5,431,766	07/1995	Propst et al.			
	5,544,772	08/1996	Soave et al.			
	5,645,684	07/1997	Keller			
	5,987,208	11/1999	Grunig			
	5,997,713	12/1999	Beetz, Jr. et al.			
	6,521,149	02/2003	Mearini et al.			
	6,526,191	02/2003	Geusic et al.			

**FOREIGN PATENT DOCUMENTS**

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
3717851		Germany			
4202454		Germany			

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

	Lehmann et al., Optical shortpass filters based on macroporous silicon <i>Appl. Phys. Lett.</i> V 78, N.5, Jan. 2001.
	J. Schilling et al., "Three-dimensional photonic crystals based on Macroporous silicon with modulated pore diameter", <i>Appl. Phys. Lett.</i> V 78, N.9, Feb. 2001
	S. Izuo et al., "A novel electrochemical etching technique for n-type silicon," <i>Sensors and Actuators A</i> 97-98 (2002), pp. 720-724
	A. Vyatkin et al., "Random and Ordered Macropore Formation in p-Type Silicon," <i>J. of the Electrochem. Soc.</i> , 149 (1), pp. G70-G76 (2002)
	H. Föll et. al, "Formation and application of porous silicon", <i>Mat. Sci. Eng.</i> R 39 (2002), pp.93-141
	S. Langa et al., "Observation of crossing pores in anodically etched n-GaAs," <i>Appl. Phys. Lett.</i> 78(8), pp.1074- 1076, (2001).
	H H. Föll et al., "Porous III-V compound semiconductors: formation, properties, and comparison to silicon", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 61-70 (2003)
	M. Christophersen et al., "A comparison of pores in silicon and pores in III-V compound materials", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 197-203, (2003)
	H. Föll et al., "Pores in III-V Semiconductors", <i>Adv. Materials, Review</i> , 2003, 15, pp.183 - 198, (2003)
	S. Langa et al., <i>Phys. Stat. Sol. A</i> , 197 (1), p. 77, (2003) "Single crystalline 2D porous arrays obtained by self organization in n-InP" (pp. 77-82)

\*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.